

P/N:YZPST-MAC97A6 97A8 Triacs

■ Feature

- ◆ Silicon triacs devices as sensitive design
- ◆ P type through diffusion isolated
- ◆ Mesa glass-passivated technology
- ◆ Back side of multi-layer metal

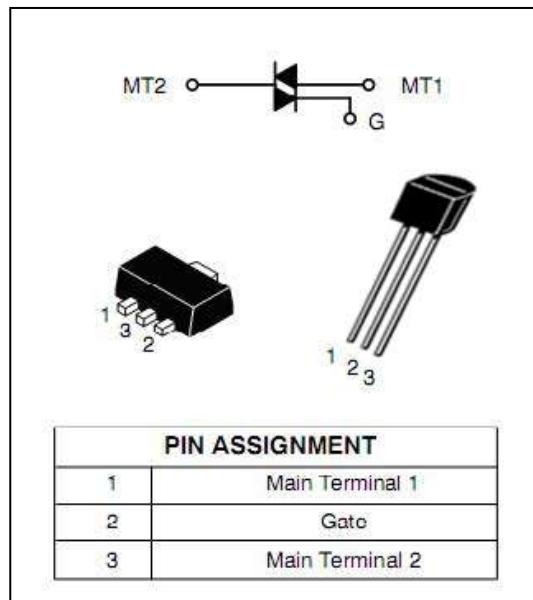
■ Typical application

- ◆ Heating controller; dimming controller
- ◆ Lamp control; Home Appliances

■ Package

- ◆ TO-92 SOT-89

■ Main Specification($T_j=25^\circ\text{C}$)



Type	Content		Value	Unit
$I_{T(\text{RMS})}$	Nominal RMS on-state Current		0.8	A
$V_{\text{DRM}}/V_{\text{RRM}}$	Off-state/reverse repetitive peak voltage	MAC97A6	400	V
		MAC97A8	600	V
I_{TSM}	Non-repetitive on-state surge current		8.0	A

■ Limited Specification

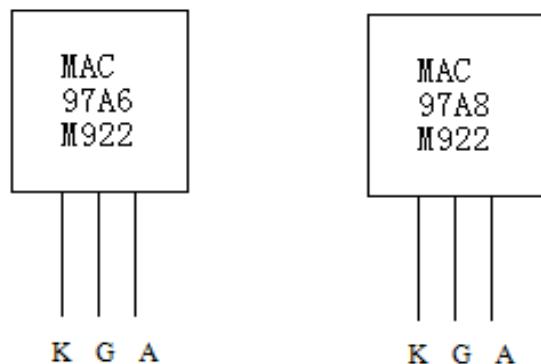
Type	Specification and conditions		value	units
$I_T(\text{RMS})$	Nominal RMS on-state Current $T_{\text{lead}} \leq 50^\circ\text{C}$		0.8	A
$V_{\text{DRM}}/V_{\text{RRM}}$	Repetitive peak off-state voltage $T_j=25^\circ\text{C}/T_c=25^\circ\text{C}$	MAC97A6	400	V
	Repetitive peak reverse voltage $T_j=25^\circ\text{C}$	MAC97A8	600	V
I_{TSM}	Non-repetitive on-state surge current sine 50HZ,one cycle $T_c=25^\circ\text{C}$		9.0	A
I^2t	Fuse current ($t_p=10\text{ms}$)		0.45	A^2S
IGM	Gate peak current		1	A
PGM	Gate peak power		1	W

PG(AV)	Gate average power	0.1	W
di/dt	Critical rate of rise of on state voltage ($I_{TM}=1\text{ A}$, $I_G=0.2\text{A}$, $d I_G /dt=0.2\text{A}/\mu\text{s}$, $T_j=110^\circ\text{C}$)	20	$\text{A}/\mu\text{s}$
T _{stg} T _j	Storage temperature Junction temperature	-40--+150 -40--+110	°C

■ Electric Characteristic ($T_j=25^\circ\text{C}$ unless show others temperature)

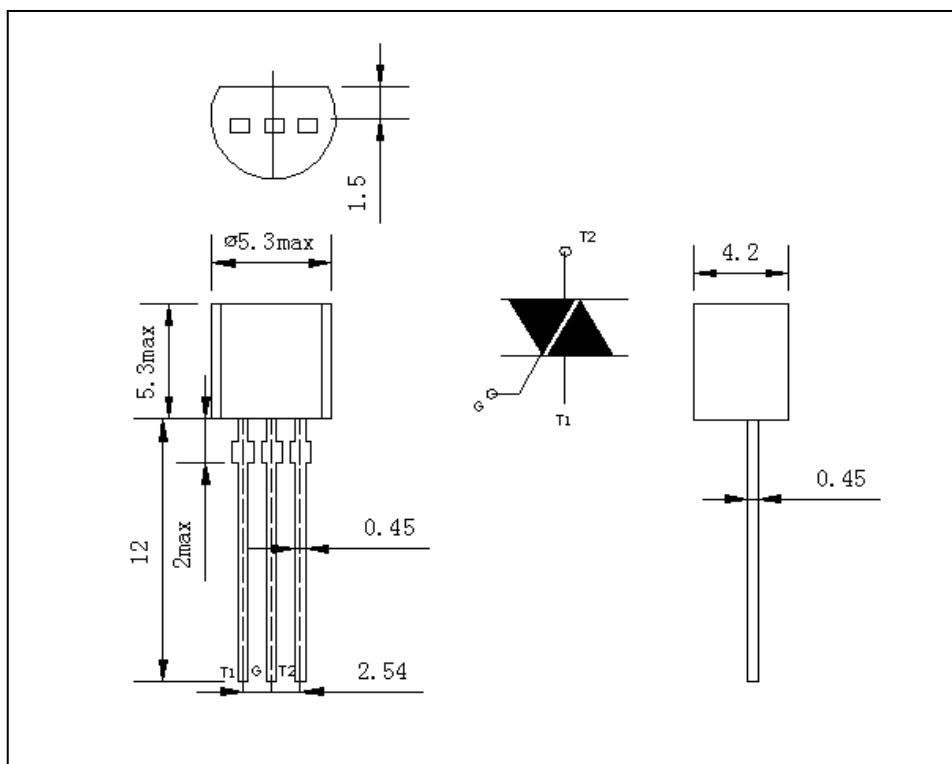
Type	Characteristics	Min	Type	Max		Unit
				A	B	
I _{GT}	Gate trigger current $V_D=12\text{V}$, $I_T=0.1\text{A}$	T2+ G+	---	---	3 5	mA
		T2+ G-	---	---	3 5	
		T2- G-	---	---	3 5	
		T2- G+	---	---	5 7	
I _L	Latch current $V_D=12\text{V}$, $I_{GT}=0.1\text{A}$	T2+ G+	---	---	10	mA
		T2+ G-	---	---	10	
		T2- G-	---	---	10	
		T2- G+	---	---	20	
I _H	Hold current $V_D=12\text{V}$, $I_{GT}=0.2\text{A}$	---	1.5	5		mA
V _{TM}	Peak on-state voltage $I_T=1.1\text{A}$	---	1.35	1.6		V
V _{GT}	Gate trigger voltage $V_D=12\text{V}$, $R_L=100\Omega$	---	0.7	1.5		V
V _{GD}	Gate non-trigger voltage, $V_D=12\text{V}$, $R_L=100\Omega$, $T_j=110^\circ\text{C}$	0.2	---	----		V
I _{DRM} I _{RRM}	$V_D=\text{Rated } V_{DRM}=\text{Rated } V_{RRM}$ $T_j=25^\circ\text{C}$ $T_j=110^\circ\text{C}$			10 0.5	$\mu\text{ A}$ mA	

■ Drawing



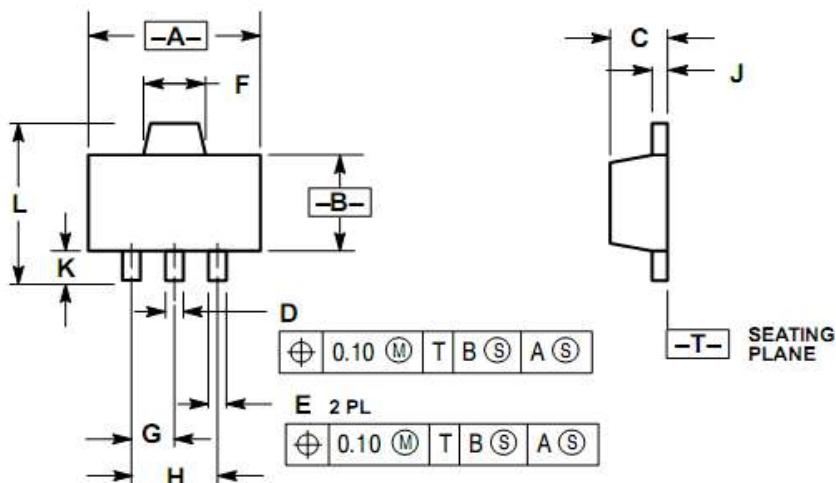
MAC97A6/8---type
6 ≥ 400V 8 ≥ 600V

■ TO-92 package drawing:



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	3.300	3.700	0.130	0.146
A1	1.100	1.400	0.043	0.055
b	0.380	0.550	0.015	0.022
c	0.360	0.510	0.014	0.020
D	4.400	4.700	0.173	0.185
D1	3.430		0.135	
E	4.300	4.700	0.169	0.185
e	1.270 TYP		0.050 TYP	
e1	2.440	2.640	0.096	0.104
L	14.100	14.500	0.555	0.571
Φ		1.600		0.063
h	0.000	0.380	0.000	0.015

SOT-89 package drawing:

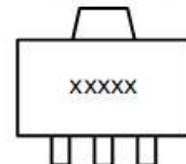


NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETERS
3. 1213-01 OBSOLETE, NEW STANDARD 1213-02.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.40	4.60	0.173	0.181
B	2.40	2.60	0.094	0.102
C	1.40	1.60	0.055	0.063
D	0.37	0.57	0.015	0.022
E	0.32	0.52	0.013	0.020
F	1.50	1.83	0.059	0.072
G	1.50 BSC		0.059 BSC	
H	3.00 BSC		0.118 BSC	
J	0.30	0.50	0.012	0.020
K	0.80	---	0.031	---
L	---	4.25	---	0.167

MARKING DIAGRAM

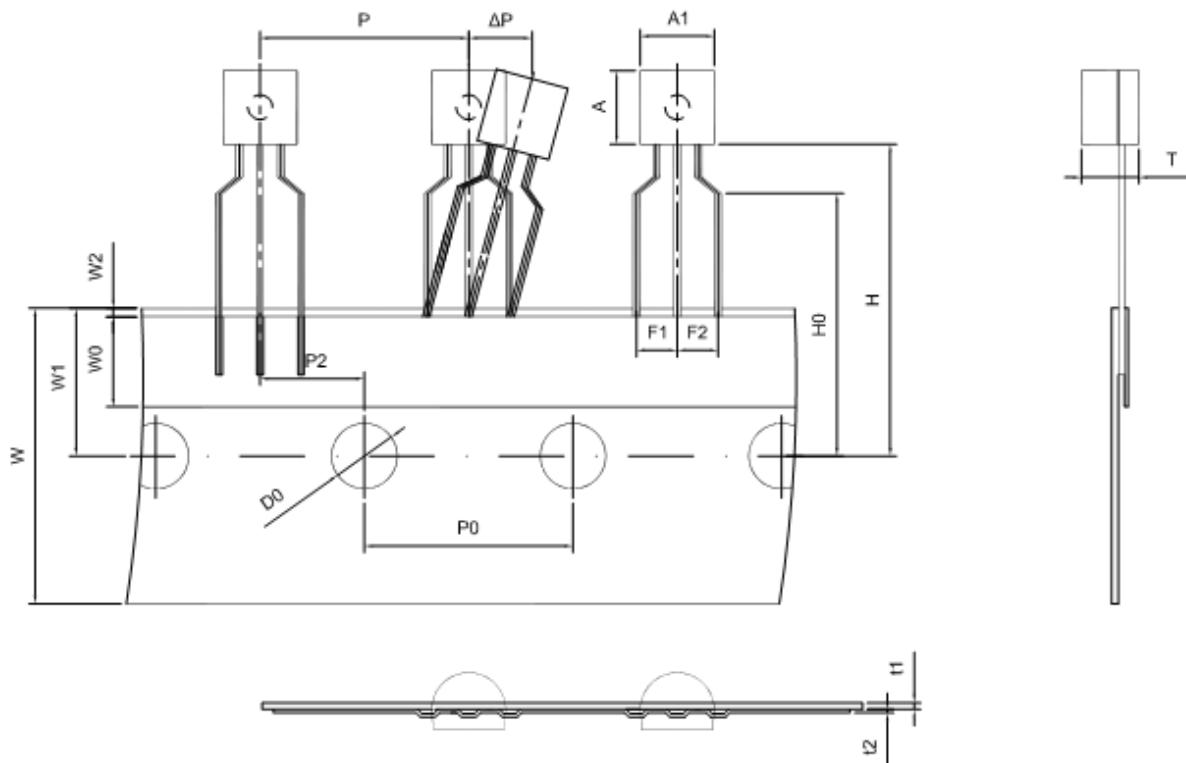


XXXXX = Specific Device Code

STYLE 1:
PIN 1. Emitter
2. Collector
3. Base

STYLE 2:
PIN 1. BASE
2. COLLECTOR
3. Emitter

TO-92 PACKAGE TAPEING DIMENSION



Dimensions are in millimeter

A1	A	T	P	P0	P2	F1	F2	W
4.5±0.2	4.5±0.2	3.5±0.2	12.7±0.3	12.7±0.2	6.35±0.3	2.5±0.3	2.5±0.3	18.0+1.0/-0.5
W0	W1	W2	H	H0	D0	t1	t2	ΔP

